

### **REMARKS/ARGUMENTS**

The Applicants originally submitted Claims 1-20 in the application. In previous responses, the Applicants withdrew Claims 7-16 and canceled Claims 4-5 and Claims 17-20 without prejudice or disclaimer. In the present response, the Applicants have amended Claim 1 and added Claims 21-22. Support for the amendment can be found, for example, in paragraphs 20-21 and 29-30 and Figures 2A and 2B of the original specification. No other Claims have been amended, canceled or added. Accordingly, Claims 1-3 and Claims 21-22 are currently pending in the application.

#### **I. Rejection of Claim 1 under 35 U.S.C. §102**

The Examiner has rejected Claim 1 under 35 U.S.C. §102(b) as being anticipated by U.S. Patent No. 5,610,790 to Staab, *et al.* The Applicants respectfully disagree.

Staab does not teach a diode circuit comprising back-to-back diodes connected at their anodes with a first cathode conductively coupled to a source region and a second cathode conductively coupled to the gate region, as recited in independent Claim 1. Instead, Staab teaches a diode **702** is formed by two diodes connected in parallel. The parallel diodes have a common anode, e.g., p type region **820**, and two n-type cathodes, e.g., n type regions **810** and **811**. (*See* column 9, lines 21-26 and Figure 8a.) Both cathodes **810** and **811** are connected to the  $V_{dd}$  power supply rail **705** which is also connected to n type region **813**, e.g., the drain of the n-channel transistor **716**. (*See* column 7, lines 4-5 and Figure 7 and column 9, lines 4-7 and Figure 8a.) Thus, Staab teaches both cathodes of a back-to-back diode circuit are coupled to a drain region, as opposed to teaching that a

first cathode is conductively coupled to a source region and a second cathode is conductively coupled to a gate region, as recited in independent Claim 1.

As such, Staab does not teach each and every element of independent Claim 1 and therefore, does not anticipate independent Claim 1. Accordingly, the Applicants respectfully request the Examiner to withdraw the §102(b) rejection with respect to Claim 1 and allow issuance thereof.

## **II. Rejection of Claims 2 and 3 under 35 U.S.C. §103**

The Examiner has rejected Claims 2 and 3 under 35 U.S.C. §103(a) as being unpatentable over Staab in view of U.S. Patent No. 6,521,515 to Kluth. The Applicants respectfully disagree.

As argued above, Staab does not teach a diode circuit comprising back-to back-diodes connected at their anodes with a first cathode conductively coupled to a source region and a second cathode conductively coupled to the gate region as recited in independent Claim 1. Furthermore, Staab does not suggest such an element. The back-to-back diodes in the claimed invention prevent any flow from source region **18** to gate metallization layer **24** that may otherwise occur during certain biasing conditions. (*See* paragraph 31.) However in Staab, the source **814** is directly coupled to the gate electrode **854** of transistor **716**. (*See* column 9, lines 10-12 and Figure 8a.) Staab has a specific configuration wherein back-to-back diodes are not connected between a source and gate region of a transistor, as is currently claimed. One skilled in the art would not be motivated to move the back-to-back diode circuit as presently claimed between the source and gate region of transistor **716** in Staab as this would frustrate the operation of the cross power supply clamp **719**. As such, Staab does not teach or suggest a diode circuit comprising back-to-back diodes connected at their

anodes with a first cathode conductively coupled to a source region and a second cathode conductively coupled to the gate region, as recited in independent Claim 1.

Kluth fails to correct the deficiencies of Staab. The Examiner is offering Kluth for the sole proposition that a conductive region can be desirably formed overlying the gate region for reducing the overall resistance of the gate electrode. (*See* Examiner's Final Rejection mailed September 19, 2006, pages 3-4.) Without even addressing the accuracy of the Examiner's offerings, a teaching or suggestion that a conductive region can be desirably formed overlying the gate region for reducing the overall resistance of the gate electrode is far from a teaching or suggestion of a diode circuit comprising back-to-back diodes connected at their anodes with a first cathode conductively coupled to a source region and a second cathode conductively coupled to the gate region, as presently claimed. Accordingly, Kluth additionally fails to teach or suggest the aforementioned claimed elements.

Thus, Staab individually or in combination with Kluth, fails to teach or suggest the invention recited in independent Claim 1 and its dependent claims, when considered as a whole. Accordingly, the cited references fail to establish a *prima facie* case of obviousness with respect to these claims. Claims 2 and 3 are therefore not obvious in view of the cited references.

In view of the foregoing remarks, the cited references do not support the Examiner's rejection of Claims 2 and 3 under 35 U.S.C. §103(a). The Applicants therefore respectfully request the Examiner to withdraw the rejection.

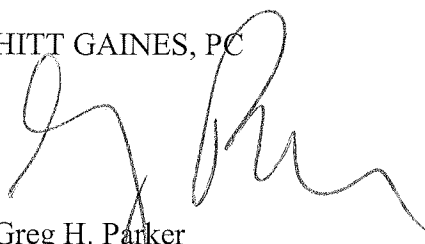
### **III. Conclusion**

In view of the foregoing amendment and remarks, the Applicants now see all of the Claims currently pending in this application to be in condition for allowance and therefore earnestly solicit a Notice of Allowance for Claims 1-3 and 21-22.

The Applicants request the Examiner to telephone the undersigned attorney of record at (972) 480-8800 if such would further or expedite the prosecution of the present application. The Commissioner is hereby authorized to charge any fees, credits or overpayments to Deposit Account 20-0668.

Respectfully submitted,

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